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NATIONAL STANDARD OF THE

PEOPLE'S REPUBLIC OF CHINA

GB/T 48163.6-2026

Semiconductor devices-Semiconductor devices for energy harvesting and generation-Part 6:Test and evaluation methods for vertical contact mode triboelectric energy harvesting devices

半导体器件 能量收集和产生半导体器件 第6部分：垂直接触模式的摩擦电能量收集器测试和评估方法

(English Translation)

Issued on: October 30, 2026 **Implemented on: May 1, 2027**

Issued by: State Administration for Market Regulation;
Standardization Administration of China

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https://chinastandards.org/standards/gb-t-48163-6-2026

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1 Foreword

GB/T 48163.6-2026 was issued by State Administration for Market Regulation; Standardization Administration of China on 30 October 2026 and takes effect on 1 May 2027.

It is one of 8 parts of the GB/T 48163 series.

The GB/T prefix marks a recommended standard. It is not law in itself: it becomes binding when a contract names it, when a regulation or a mandatory standard refers to it, or when a producer declares conformity with it.

2 Scope Preview

GB/T 48163.6-2026 carries no ICS number and no Chinese Standard Classification code.

This catalogue holds 76,457 other GB/T standards.

Of the 47,415 GB/T standards that do carry an ICS number, 3,437 (7%) fall under ICS 77, in the field of metallurgy.

3 About this standard

Issued by: State Administration for Market Regulation; Standardization Administration of China

4 Related standards

Other parts of this standard:

GB/T 48163.1-2026 - Semiconductor devices - Semiconductor devices for energy harvesting and generation - Part 1: Vibration based piezoelectric energy harvesting

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GB/T 48163.2-2026 - Semiconductor devices - Semiconductor devices for energy harvesting and generation - Part 2: Thermo power based thermoelectric energy harvesting

GB/T 48163.3-2026 - Semiconductor devices - Semiconductor devices for energy harvesting and generation - Part 3: Vibration based electromagnetic energy harvesting

GB/T 48163.4-2026 - Semiconductor devices-Semiconductor devices for energy harvesting and generation-Part 4: Test and evaluation methods for flexible piezoelectric energy harvesting devices

GB/T 48163.5-2026 - Semiconductor devices-Semiconductor devices for energy harvesting and generation-Part 5:Test method for measuring generated power from flexible thermoelectric devices

GB/T 48163.7-2026 - Semiconductor devices-Semiconductor devices for energy harvesting and generation-Part 7:Linear sliding mode triboelectric energy harvesting

GB/T 48163.8-2026 - Semiconductor devices - Semiconductor devices for energy harvesting and generation - Part 8: Test and evaluation methods of flexible and stretchable supercapacitors for use in low power electronics

5 Classification and status

Prefix GB/T: recommended standard.

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